

COMPONENT FOR FABRICATING SiC SEMICONDUCTOR, HAVING
PLURALITY OF LAYERS HAVING DIFFERENT TRANSMITTANCES, AND
METHOD FOR MANUFACTURING THE SAME

[ABSTRACT]

Provided according to an embodiment of the present invention is a component for fabricating an SiC semiconductor, having a plurality of layers having different transmittances, the component comprising two or more superposed layers, wherein each of the superposed layers contains SiC and has a transmittance value different from that of another adjacent layer.

Fig. 6